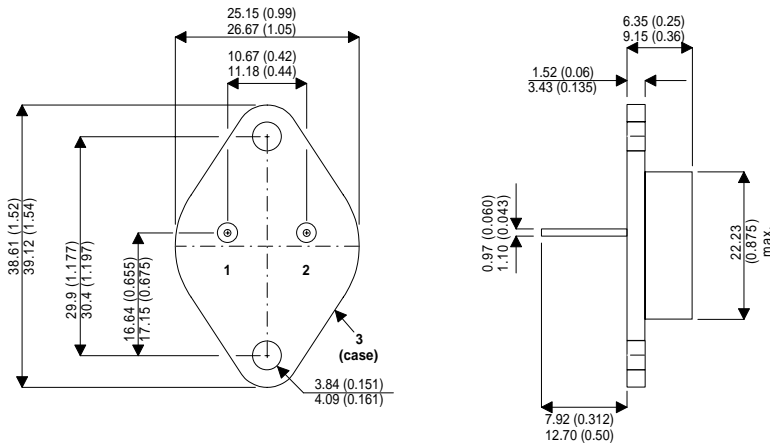


TO-3 (TO-204AA) Package Outline.
Dimensions in mm (inches)

4TH GENERATION MOSFET

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS



Pin 1 – Gate

Pin 2 – Source

Case – Drain

V_{DSS} **1000V**
 $I_{D(cont)}$ **6.0A**
 $R_{DS(on)}$ **2.00 Ω**

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	1000	V
I_D	Continuous Drain Current	6.0	A
I_{DM}	Pulsed Drain Current ¹	24	A
V_{GS}	Gate – Source Voltage	± 30	V
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	198	W
	Derate Linearly	1.584	W/ $^{\circ}C$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^{\circ}C$
T_L	Lead Temperature : 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0V$)	$V_{DS} = V_{DSS}$			250	μA
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}C$			1000	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V
$I_{D(ON)}$	On State Drain Current ²	$V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max $V_{GS} = 10V$	6.0			A
$R_{DS(ON)}$	Drain – Source On State Resistance ²	$V_{GS} = 10V, I_D = 0.5 I_D [Cont.]$			2.00	Ω

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 μS , Duty Cycle < 2%

DYNAMIC CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		1530	1800	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		230	325	
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		80	120	
Q_g	Total Gate Charge ³	$V_{GS} = 10V$		66	105	nC
Q_{gs}	Gate – Source Charge	$V_{DD} = 0.5 V_{DSS}$		6.5	10	
Q_{gd}	Gate – Drain (“Miller”) Charge	$I_D = I_D [Cont.] @ 25^\circ C$		36	54	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$		14	28	ns
t_r	Rise Time	$V_{DD} = 0.5 V_{DSS}$		13	26	
$t_{d(off)}$	Turn-off Delay Time	$I_D = I_D [Cont.] @ 25^\circ C$		55	82	
t_f	Fall Time	$R_G = 1.8\Omega$		19	37	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	(Body Diode)			6.0	A
I_{SM}	Pulsed Source Current ¹	(Body Diode)			24	
V_{SD}	Diode Forward Voltage ²	$V_{GS} = 0V, I_S = -I_D [Cont.]$			1.3	V
t_{rr}	Reverse Recovery Time	$I_S = -I_D [Cont.], di_S / dt = 100A/\mu s$	225	450	910	ns
Q_{rr}	Reverse Recovery Charge	$I_S = -I_D [Cont.], di_S / dt = 100A/\mu s$	1.2	2.5	5	μC

SAFE OPERATING AREA CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
SOA1	Safe Operating Area	$V_{DS} = 0.4V_{DSS}, t = 1 Sec.$ $I_{DS} = P_D / 0.4V_{DSS}$	198			W
SOA2	Safe Operating Area	$V_{DS} = P_D / I_D [Cont.]$ $I_{DS} = I_D [Cont.], t = 1 Sec.$	198			W
I_{LM}	Inductive Current Clamped		24			A

THERMAL CHARACTERISTICS

	Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction to Case			0.63	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			30	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 μs , Duty Cycle < 2%

3) See MIL–STD–750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.